

20V P-Channel MOSFET



SOT-23



Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)	
-20	130 @ V _{GS} = -4.5V	-2.8	
	190 @ V _{GS} = -2.5V	-2.0	

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

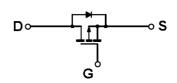
- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM2301CX RFG	SOT-23	3Kpcs / 7" Reel

Note: "G" denotes for Halogen Free

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	-2.8	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-8	Α	
Continuous Source Current (Diode Co	onduction) ^{a,b}	I _S	I _S -0.72		
Maximum Power Dissipation	Ta = 25°C	P _D	0.9	W	
	Ta = 75°C		0.57		
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T_{J}, T_{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T _L	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	RO _{JA}	120	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.
- c. Surface Mounted on FR4 Board,



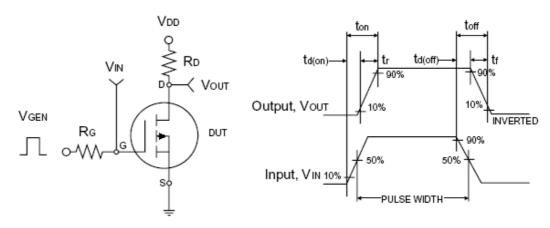
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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.45		-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -9.6V, V_{GS} = 0V$	I _{DSS}			-1.0	μΑ
On-State Drain Current ^a	$V_{DS} = -10V, V_{GS} = -5V$	I _{D(ON)}	-6			Α
Drain-Source On-State Resistance ^a	V _{GS} = -4.5V, I _D = -2.8A		85	130	0	
Diain-Source On-State Resistance	$V_{GS} = -2.5V, I_{D} = -2.0A$	R _{DS(ON)}		122	190	mΩ
Forward Transconductance ^a	$V_{DS} = -5V, I_{D} = -4A$	g _{fs}	1	6.5		S
Diode Forward Voltage	$I_S = -0.75A$, $V_{GS} = 0V$	V_{SD}	-	- 0.8	-1.2	V
Dynamic ^b					_	
Total Gate Charge	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Q_{g}		5.4	10	
Gate-Source Charge	$V_{DS} = -6V, I_D = -2.8A,$ $V_{GS} = -4.5V$	Q_{gs}		0.8		nC
Gate-Drain Charge	V _{GS} = -4.5V	Q_{gd}		1.1		
Input Capacitance		C _{iss}		447		
Output Capacitance	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		127		pF
Reverse Transfer Capacitance	T = T.UIVIMZ	C _{rss}		80		
Switching ^c						
Turn-On Delay Time	., ., .	t _{d(on)}	1	5	25	
Turn-On Rise Time	$V_{DD} = -6V, R_{L} = 6\Omega,$	t _r		19	60	0
Turn-Off Delay Time	$I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$	t _{d(off)}		95	110	nS
Turn-Off Fall Time	116 - 022	t _f		65	80	

- a. pulse test: PW = $300\mu S$, duty cycle = 2% b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

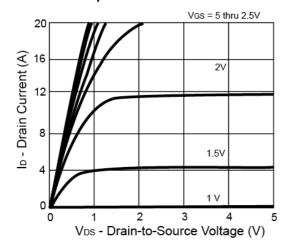


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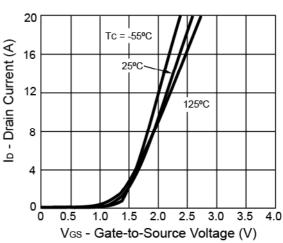


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

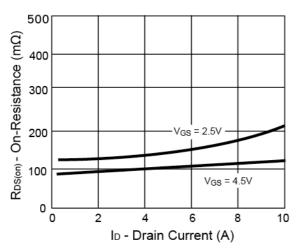
Output Characteristics



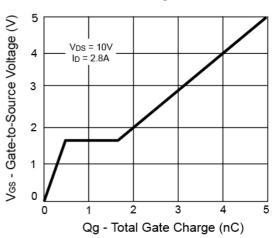
Transfer Characteristics



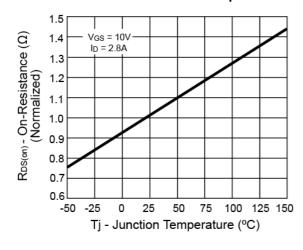
On-Resistance vs. Drain Current



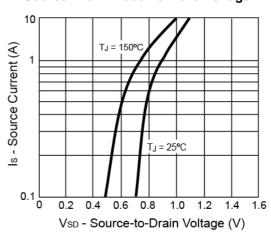
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



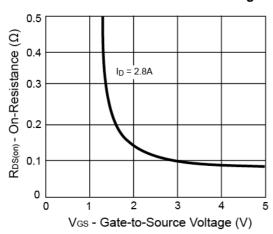


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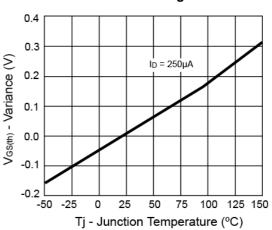


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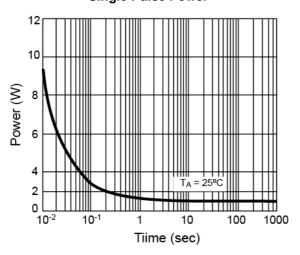
On-Resistance vs. Gate-Source Voltage



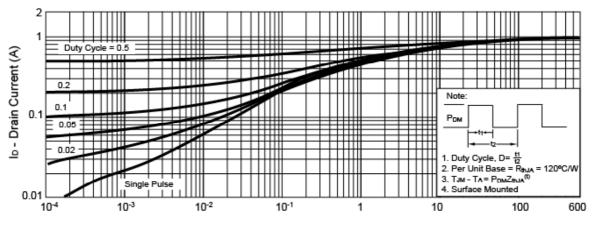
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



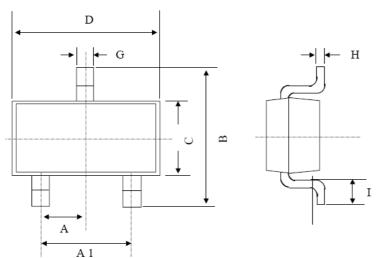
Square Wave Pulse Duration (sec)



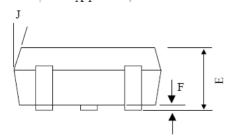
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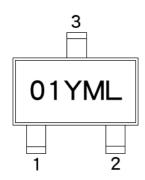
SOT-23 Mechanical Drawing



	SOT-23 DIMENSION				
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037	'BSC	
A1	1.9	1.9 BSC 0.074 BSC		BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



Marking Diagram



01 = Device Code

Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



TSM2301 20V P-Channel MOSFET

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